

**2N499**  
**GERMANIUM**  
**MICRO ALLOY**  
**DIFFUSED-BASE**  
**TRANSISTOR**  
**PNP POLARITY**

I. General Description

This transistor is a PNP, germanium, triode transistor designed primarily for low power IF and RF amplifier applications in the up to 100mc frequency range for industrial service.

II. Mechanical Data

- A. Outline drawing TO-1
- B. Terminal Designations

<u>Terminal</u>	<u>Element</u>
1	Emitter
2	Base
3	Collector
Case	All leads insulated from case

III. Absolute Maximum Ratings

A. Maximum Temperature

- 1. Storage Temperature -65°C to +100°C
- 2. Lead Temperature, 1/16"  $\pm$  1/32" from case for 10 seconds 230°C

B. Maximum Reverse Rating (T = 25°C)

- 1. Emitter-base, V<sub>EBO</sub> -0.5 volt
- 2. Collector-base, V<sub>CBO</sub> - 30 volts
- 3. Collector-emitter, V<sub>CEO</sub> - 18 volts

C. Maximum Current (DC)

- 1. Collector Current, I<sub>C</sub> - 50 ma

D. Power

- 1. Maximum Power Dissipation (T = 25°C) 60 mW
- 2. Derating Factor above 25°C 0.8 mW/°C